

Nch 800V 8A Power MOSFET

| V_{DSS} | 800V |
|----------------------------|-------|
| R _{DS(on)} (Max.) | 1.03Ω |
| I _D | ±8A |
| P_D | 66W |

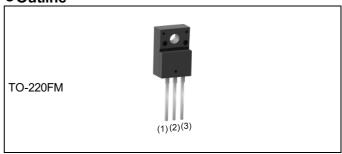
● Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

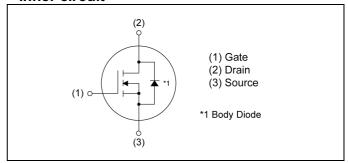
Application

Switching Power Supply

Outline



•Inner circuit



Packaging specifications

| | Packing | Bulk |
|------|---------------------------|----------|
| | Reel size (mm) | - |
| _ | Tape width (mm) | - |
| Type | Basic ordering unit (pcs) | 500 |
| | Taping code | - |
| | Marking | R8008ANX |

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

| Parameter | Symbol | Value | Unit | |
|--------------------------------------------------|------------------------|--------------------|-------------|------|
| Drain - Source voltage | | V_{DSS} | 800 | V |
| Continuous dusin surrount | T _C = 25°C | I _D *1 | ±8 | Α |
| Continuous drain current | T _C = 100°C | I _D *1 | ±3.9 | Α |
| Pulsed drain current | | I _{DP} *2 | ±32 | Α |
| Gate - Source voltage | | V_{GSS} | ±30 | V |
| Avalanche current, single pulse | | I _{AS} *3 | 4 | Α |
| Avalanche energy, single pulse | E _{AS} *3 | 4.2 | mJ | |
| Avalanche energy, repetitive | | E _{AR} *4 | 3.3 | mJ |
| Power dissipation (T _c = 25°C) | P _D | 66 | W | |
| Junction temperature | T _j | 150 | °C | |
| Operating junction and storage temperature range | | T _{stg} | -55 to +150 | °C |
| Reverse diode dv/dt | | dv/dt | 15 | V/ns |

● Absolute maximum ratings

| Parameter | Symbol | Conditions | Values | Unit |
|------------------------------|--------|-------------------------------------------------------|--------|------|
| Drain - Source voltage slope | dv/dt | $V_{DS} = 640V, I_{D} = 8A$ $T_{j} = 125^{\circ}C$ | 50 | V/ns |

●Thermal resistance

| Doromotor | Symbol | Values | | | Linit |
|----------------------------------------------|-------------------|--------|------|------|-------|
| Parameter | Symbol | Min. | Тур. | Max. | Unit |
| Thermal resistance, junction - case | R _{thJC} | - | - | 1.87 | °C/W |
| Thermal resistance, junction - ambient | R _{thJA} | - | - | 70 | °C/W |
| Soldering temperature, wavesoldering for 10s | T _{sold} | - | - | 265 | °C |

• Electrical characteristics $(T_a = 25^{\circ}C)$

| Parameter | Cumb al | Conditions | Values | | | Unit |
|------------------------------------------------|------------------------|-----------------------------------------------------------------------|--------|--------------|-------------|-------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Offic |
| Drain - Source breakdown voltage | V _{(BR)DSS} | $V_{GS} = 0V$, $I_D = 1mA$ | 800 | - | 1 | V |
| Drain - Source avalanche breakdown voltage | V _{(BR)DS} | $V_{GS} = 0V$, $I_D = 4A$ | - | 900 | - | V |
| Zero gate voltage drain current | I _{DSS} | $V_{DS} = 800V, V_{GS} = 0V$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$ | - | 0.1 | 100 1000 | μА |
| Gate - Source leakage current | I _{GSS} | V _{GS} = ±30V, V _{DS} = 0V | - | - | ±100 | nA |
| Gate threshold voltage | V _{GS(th)} | V _{DS} = 10V, I _D = 1mA | 3 | - | 5 | V |
| Static drain - source on - state resistance | R _{DS(on)} *6 | $V_{GS} = 10V, I_D = 4.0A$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$ | - | 0.79 1.54 | 1.03 | Ω |
| Gate resistance | R_{G} | f = 1MHz, open drain | - | 6.6 | - | Ω |

● Electrical characteristics (T_a = 25°C)

| Davamatar | Cymah ol | Conditions | Values | | | Lloit |
|----------------------------------------------|------------------------|-----------------------------------------------|--------|------|------|-------|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
| Forward Transfer Admittance | Y _{fs} *6 | V _{DS} = 10V, I _D = 4A | 2.0 | 4.0 | - | S |
| Input capacitance | C _{iss} | V _{GS} = 0V | - | 1080 | - | |
| Output capacitance | C _{oss} | V _{DS} = 25V | - | 480 | - | pF |
| Reverse transfer capacitance | C _{rss} | f = 1MHz | | 32 | - | |
| Effective output capacitance, energy related | C _{o(er)} | V _{GS} = 0V, | - | 30.2 | - | - F |
| Effective output capacitance, time related | C _{o(tr)} | V _{DS} = 0V to 640V | - | 78.8 | - | pF |
| Turn - on delay time | t _{d(on)} *6 | V _{DD} ≈ 400V, V _{GS} = 10V | - | 32 | - | |
| Rise time | t _r *6 | I _D = 4.0A | - | 50 | - | |
| Turn - off delay time | t _{d(off)} *6 | R _L ≃ 100Ω | - | 85 | 170 | ns |
| Fall time | t _f *6 | $R_G = 10\Omega$ | - | 30 | 60 | |

● Gate charge characteristics (T_a = 25°C)

| Parameter | Symbol | Conditions | Values | | | 1.134 |
|----------------------|------------------------|---------------------------------------------|--------|------|------|-------|
| | | Conditions | Min. | Тур. | Max. | Unit |
| Total gate charge | Q_g^{*6} | V _{DD} ≃ 400V | - | 39 | - | |
| Gate - Source charge | Q _{gs} *6 | I _D = 8A | - | 8.7 | - | nC |
| Gate - Drain charge | Q _{gd} *6 | V _{GS} = 10V | - | 23 | - | |
| Gate plateau voltage | V _(plateau) | V _{DD} ≃ 400V, I _D = 8A | - | 7.3 | - | V |

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw ≤ 10µs, Duty cycle ≤ 1%

^{*3} L $^{\sim}$ 500 μ H, V_{DD}=50V, R_G=25 Ω , starting T_j=25 $^{\circ}$ C

^{*4} L $^{\sim}500\mu\text{H},\,V_{DD}$ =50V, R_G=25 Ω , starting T_i=25°C, f=10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

| Darameter | Symbol | Canditions | | Limit | | | |
|-----------------------------------------------|----------------------|----------------------------------------|------|-------|------|------|--|
| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit | |
| Continuous forward current | I _S *1 | T - 25°C | - | - | 8 | А | |
| Pulse forward current | I _{SP} *2 | T _C = 25°C | - | - | 32 | А | |
| Forward voltage | V_{SD}^{*6} | $V_{GS} = 0V, I_{S} = 8A$ | - | - | 1.5 | V | |
| Reverse recovery time | t _{rr} *6 | | - | 625 | - | ns | |
| Reverse recovery charge | Q _{rr} *6 | I _S = 8A di/dt = 100A/µs | - | 7.03 | - | μC | |
| Peak reverse recovery current | I _{rm} *6 | - αι/αι – 100/-γμ3 | - | 22.5 | - | Α | |
| Peak rate of fall of reverse recovery current | di _{rr} /dt | T _j = 25°C | - | 90 | - | A/µs | |

● Typical transient thermal characteristics

| Symbol | Value | Unit |
|------------------|-------|------|
| R _{th1} | 0.144 | |
| R _{th2} | 0.72 | K/W |
| R _{th3} | 2.15 | |

| Symbol | Value | Unit |
|------------------|---------|------|
| C _{th1} | 0.00267 | |
| C _{th2} | 0.0348 | Ws/K |
| C _{th3} | 0.491 | |

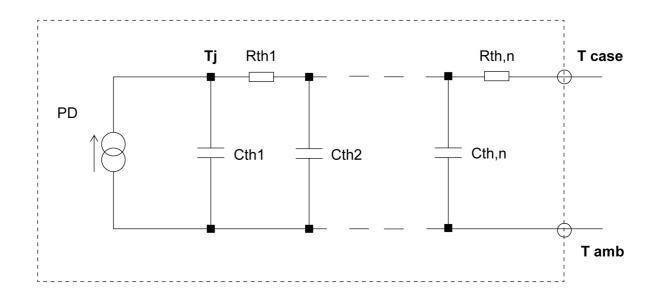


Fig.1 Power Dissipation Derating Curve

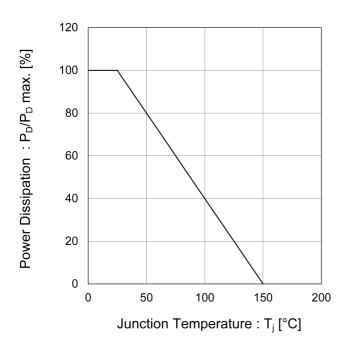
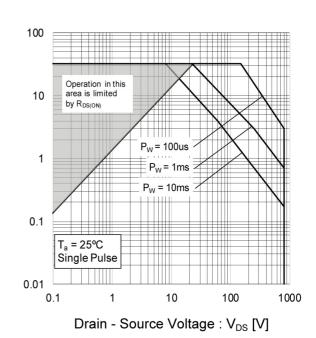
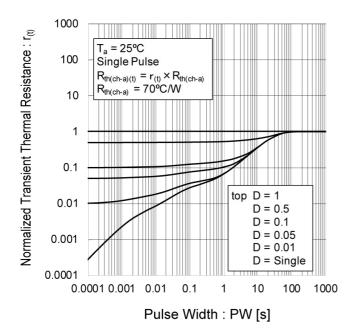


Fig.2 Maximum Safe Operating Area



Drain Current : I_D [A]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Avalanche Current : IAR [A]

• Electrical characteristic curves

Fig.4 Avalanche Current vs. Inductive Load

Fig.5 Avalanche Power Losses

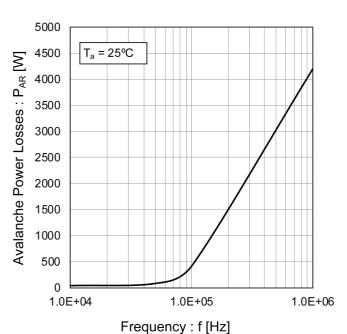


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

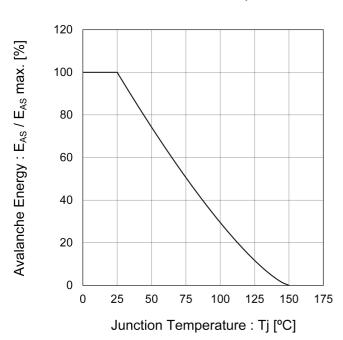
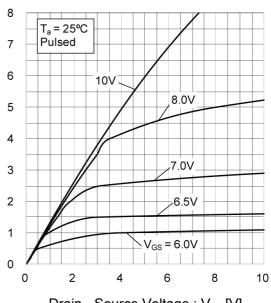


Fig.7 Typical Output Characteristics(I)

8 T_a = 25°C Pulsed 7 6 Drain Current : I_D [A] 8.0V 5 4 7.0V 3 6.5V 2 1 $V_{GS} = 6.0V$ 0 0 10 20 30 50 Drain - Source Voltage: V_{DS} [V]

Fig.8 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

Fig.9 Tj = 150°C Typical Output Characteristics (I)

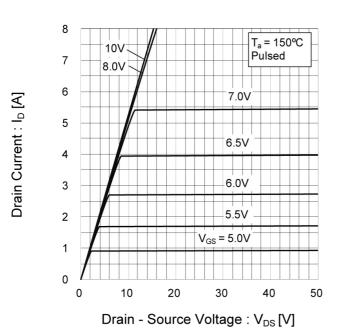
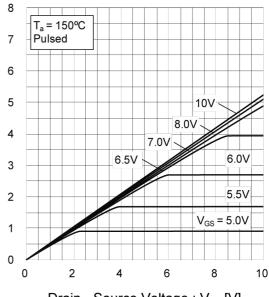


Fig.10 Tj = 150°C Typical Output Characteristics (II)



Drain Current : I_D [A]

Drain Current : I_D [A]

Fig.11 Breakdown Voltage vs. Junction Temperature

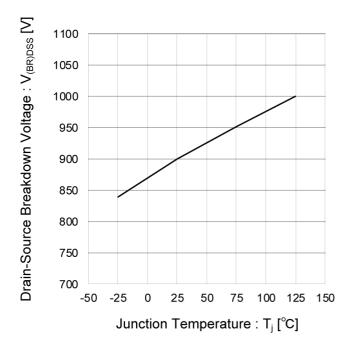


Fig.12 Typical Transfer Characteristics

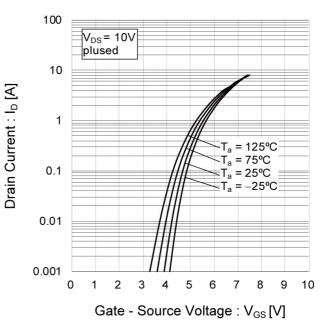


Fig.13 Gate Threshold Voltage vs. Junction Temperature

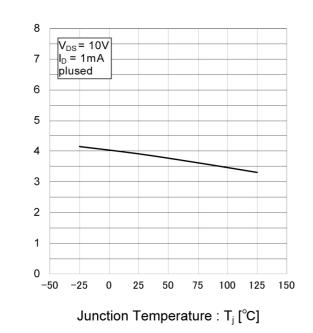
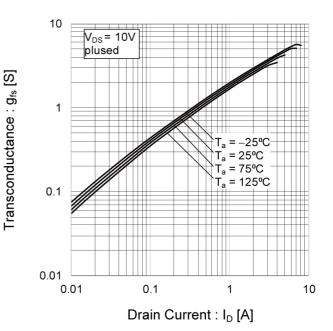


Fig.14 Transconductance vs. Drain Current



Gate Threshold Voltage: VGS(th) [V]

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Static Drain - Source On-Static Drain - Static Drai

Gate - Source Voltage : V_{GS} [V]

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

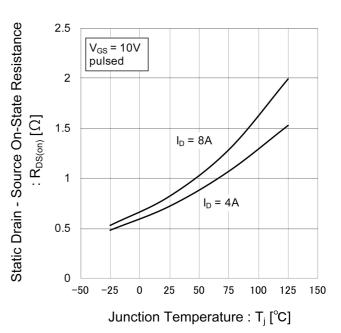


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

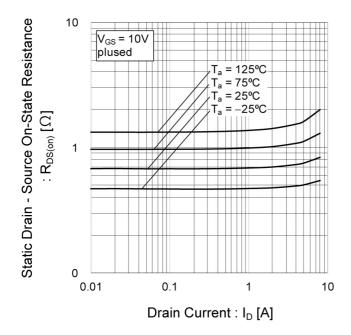
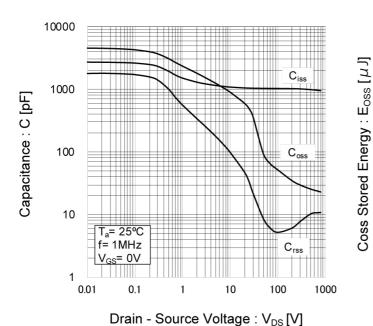


Fig.18 Typical Capacitance vs. Drain -Source Voltage



12

0

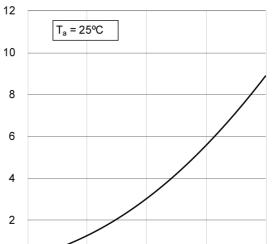


Fig.19 Coss Stored Energy

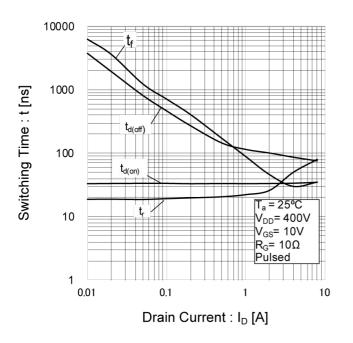
Drain - Source Voltage : V_{DS} [V]

400

600

800

Fig.20 Switching Characteristics



Gate - Source Voltage : V_{GS} [V]

Fig.21 Dynamic Input Characteristics

200

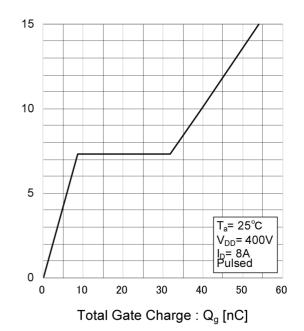


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

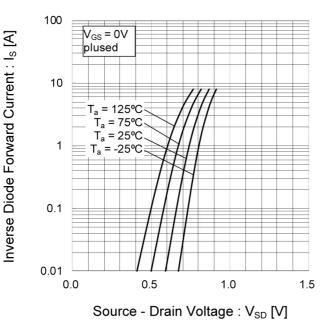
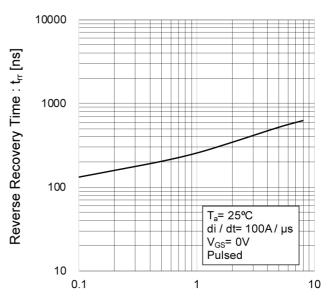


Fig.23 Reverse Recovery Time vs.
Inverse Diode Forward Current



Inverse Diode Forward Current: I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

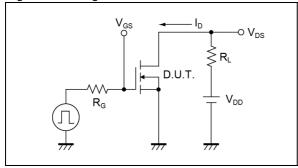


Fig.2-1 Gate Charge Measurement Circuit

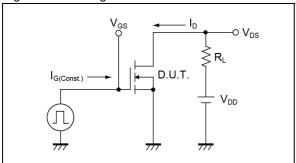


Fig.3-1 Avalanche Measurement Circuit

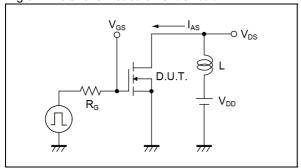


Fig.4-1 dv/dt Measurement Circuit

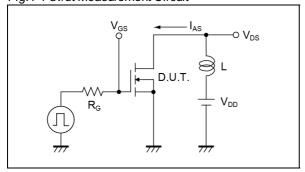


Fig.5-1 di/dt Measurement Circuit

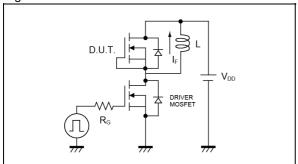


Fig.1-2 Switching Waveforms

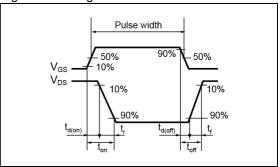


Fig.2-2 Gate Charge Waveform

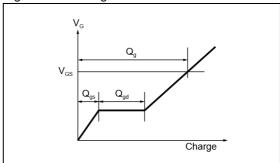


Fig.3-2 Avalanche Waveform

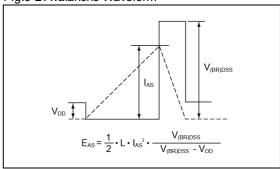


Fig.4-2 dv/dt Waveform

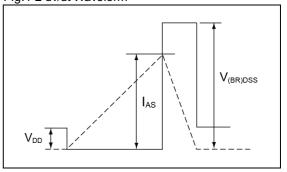
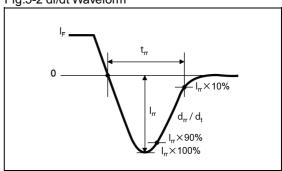
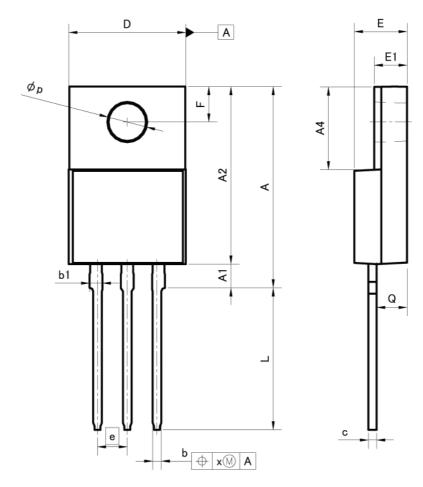


Fig.5-2 di/dt Waveform



Dimensions

TO-220FM



| DIM | MILIM | ETERS | INC | HES |
|-----|------------|-------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 16.60 | 17.60 | 0.654 | 0.693 |
| A1 | 1.80 | 2.20 | 0.071 | 0.087 |
| A2 | 14.80 | 15.40 | 0.583 | 0.606 |
| A4 | 6.80 | 7.20 | 0.268 | 0.283 |
| b | 0.70 | 0.90 | 0.028 | 0.035 |
| b1 | 1.10 | 1.50 | 0.043 | 0.059 |
| С | 0.70 | 0.85 | 0.028 | 0.033 |
| D | 9.90 | 10.30 | 0.390 | 0.406 |
| E | 4.40 | 4.80 | 0.173 | 0.189 |
| е | 2. | 54 | 0.1 | 00 |
| E1 | 2.70 | 3.00 | 0.106 | 0.118 |
| F | 2.80 | 3.20 | 0.110 | 0.126 |
| L | 11.50 | 12.50 | 0.453 | 0.492 |
| р | 3.00 | 3.40 | 0.118 | 0.134 |
| Q | 2.10 | 3.10 | 0.083 | 0.122 |
| Х | W _ | 0.38 | _ | 0.015 |

Dimension in mm/inches



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| JÁPAN | USA | EU | CHINA |
|---------|---------|------------|----------|
| CLASSⅢ | CLASSII | CLASS II b | CLASSIII |
| CLASSIV | | CLASSⅢ | |

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 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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Notice-PGA-E Rev.003



R8008ANX - Web Page

Distribution Inventory

| Part Number | R8008ANX |
|-----------------------------|----------|
| Package | TO-220FM |
| Unit Quantity | 500 |
| Minimum Package Quantity | 500 |
| Packing Type | Bulk |
| Constitution Materials List | inquiry |
| RoHS | Yes |